

MOSFETs Silicon N-Channel MOS ( $\pi$ -MOSVII)

# TK3P50D

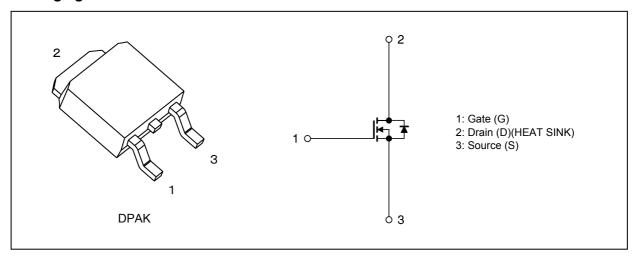
#### 1. Applications

• Switching Voltage Regulators

#### 2. Features

- (1) Low drain-source on-resistance:  $R_{DS(ON)} = 2.3 \Omega$  (typ.)
- (2) High forward transfer admittance:  $|Y_{fs}| = 1.0 \text{ S (typ.)}$
- (3) Low leakage current:  $I_{DSS} = 10 \mu A \text{ (max) (V}_{DS} = 500 \text{ V)}$
- (4) Enhancement mode:  $V_{th} = 2.4$  to 4.4 V ( $V_{DS} = 10$  V,  $I_D = 1$  mA)

#### 3. Packaging and Internal Circuit



### 4. Absolute Maximum Ratings (Note) (Ta = 25°C unless otherwise specified)

Characteristics	Symbol	Rating	Unit	
Drain-source voltage		$V_{DSS}$	500	V
Gate-source voltage		$V_{GSS}$	±30	
Drain current (DC)	(Note 1)	I <sub>D</sub>	3	Α
Drain current (pulsed)	(Note 1)	I <sub>DP</sub>	6	
Power dissipation (T <sub>c</sub> = 25°C)		P <sub>D</sub>	60	W
Single-pulse avalanche energy	(Note 2)	E <sub>AS</sub>	81	mJ
Avalanche current		I <sub>AR</sub>	3	Α
Repetitive avalanche energy	(Note 3)	E <sub>AR</sub>	6	mJ
Channel temperature		T <sub>ch</sub>	150	°C
Storage temperature		T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Start of commercial production



#### 5. Thermal Characteristics

Characteristics	Symbol	Max	Unit
Channel-to-case thermal resistance	R <sub>th(ch-c)</sub>	2.08	°C/W
Channel-to-ambient thermal resistance	R <sub>th(ch-a)</sub>	125	

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2:  $V_{DD}$  = 90 V,  $T_{ch}$  = 25°C (initial), L = 15.3 mH,  $R_G$  = 25  $\Omega$ ,  $I_{AR}$  = 3 A

Note 3: Repetitive rating; pulse width limited by maximum channel temperature

Note: This transistor is sensitive to electrostatic discharge and should be handled with care.



#### 6. Electrical Characteristics

### 6.1. Static Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0 \text{ V}$	_	_	±1	μА
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = 500 V, V <sub>GS</sub> = 0 V	_	_	10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = 10 mA, V <sub>GS</sub> = 0 V	500	_	_	V
Gate threshold voltage	$V_{th}$	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1 mA	2.4	_	4.4	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 1.5 A	_	2.3	3.0	Ω
Forward transfer admittance	Y <sub>fs</sub>	V <sub>DS</sub> = 10 V, I <sub>D</sub> = 1.5 A	0.3	1		S

### 6.2. Dynamic Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = 25 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	280	_	pF
Reverse transfer capacitance	C <sub>rss</sub>		_	1.5	_	
Output capacitance	C <sub>oss</sub>		_	30	_	
Switching time (rise time)	t <sub>r</sub>	See Figure 6.2.1.	_	20	_	ns
Switching time (turn-on time)	t <sub>on</sub>		_	50	_	
Switching time (fall time)	t <sub>f</sub>		_	10	_	
Switching time (turn-off time)	t <sub>off</sub>		_	80	_	

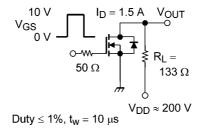


Fig. 6.2.1 Switching Time Test Circuit

### 6.3. Gate Charge Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	$Q_g$	$V_{DD} \approx 400 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 3 \text{ A}$	_	7		nC
Gate-source charge	$Q_{gs}$			4		
Gate-drain charge	$Q_{gd}$		_	3		

### 6.4. Source-Drain Characteristics (T<sub>a</sub> = 25°C unless otherwise specified)

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Reverse drain current (DC)	(Note 1)	I <sub>DR</sub>	_	_	_	3	Α
Reverse drain current (pulsed)	(Note 1)	I <sub>DRP</sub>	_		_	6	
Diode forward voltage		V <sub>DSF</sub>	I <sub>DR1</sub> = 3 A, V <sub>GS</sub> = 0 V	_	_	-1.7	V
Reverse recovery time		t <sub>rr</sub>	I <sub>DR</sub> = 3 A, V <sub>GS</sub> = 0 V	_	770	_	ns
Reverse recovery charge		Q <sub>rr</sub>	-dI <sub>DR</sub> /dt = 100 A/μs		2.5	1	μС



# 7. Marking

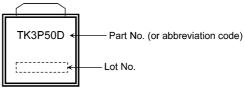
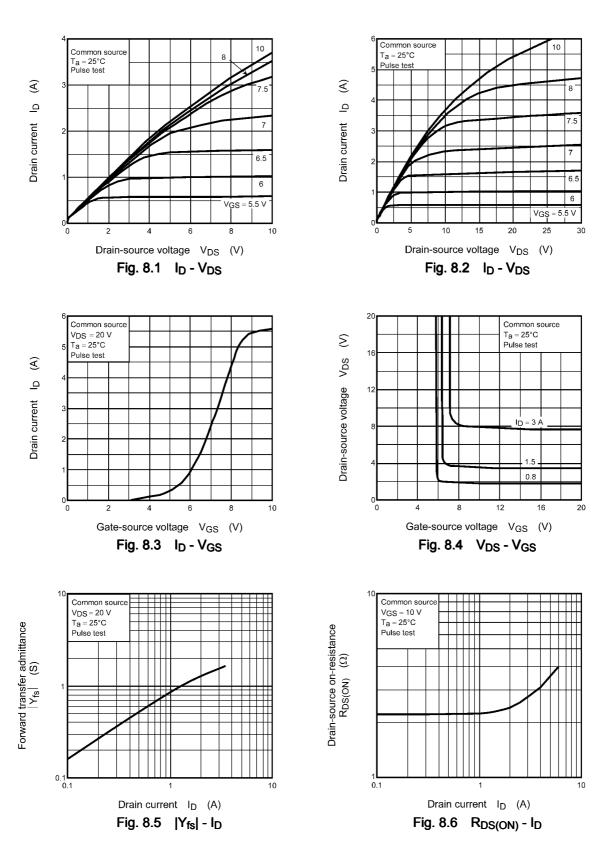


Fig. 7.1 Marking

### 8. Characteristics Curves (Note)



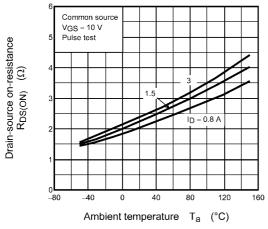
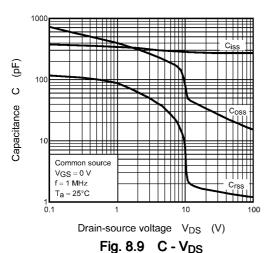


Fig. 8.7 R<sub>DS(ON)</sub> - T<sub>a</sub>



Case temperature T<sub>c</sub> (°C)

Fig. 8.11 P<sub>D</sub> - T<sub>c</sub> (Guaranteed Maximum)

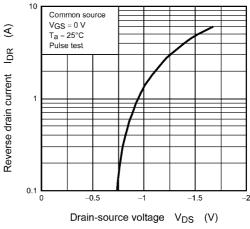


Fig. 8.8 I<sub>DR</sub> - V<sub>DS</sub>

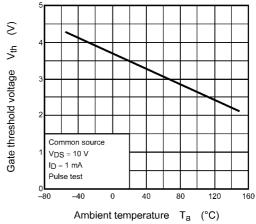


Fig. 8.10 V<sub>th</sub> - T<sub>a</sub>

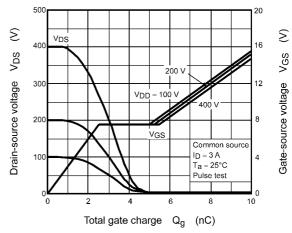


Fig. 8.12 Dynamic Input/Output Characteristics

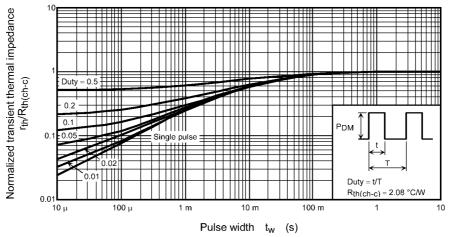


Fig. 8.13  $r_{th}/R_{th(ch-c)} - t_w$  (Guaranteed Maximum)

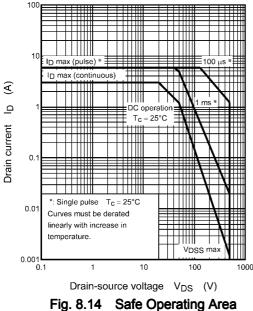


Fig. 8.14 Safe Operating Area (Guaranteed Maximum)

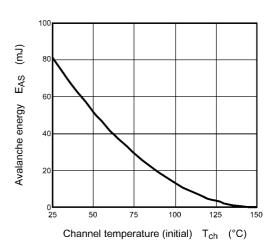


Fig. 8.15 E<sub>AS</sub> - T<sub>ch</sub> (Guaranteed Maximum)

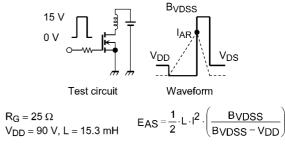


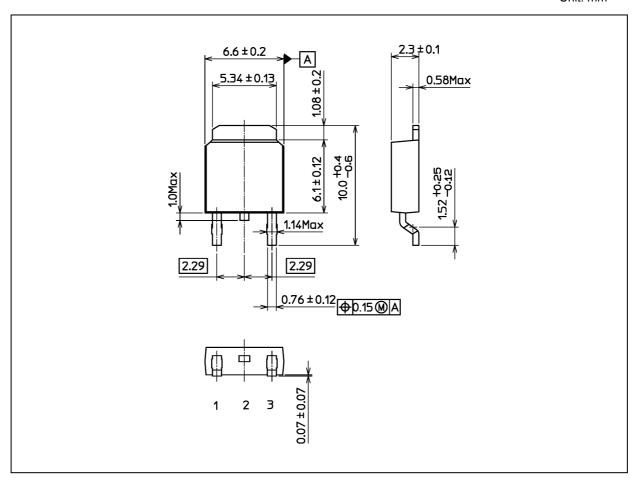
Fig. 8.16 Test Circuit/Waveform

Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.



### **Package Dimensions**

Unit: mm



Weight: 0.36 g (typ.)

	Package Name(s)
TOSHIBA: 2-7K1S	
Nickname: DPAK	



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